**Recipes:**

A. Resist Type: PMMA (+ve) e-beam resist

Supplier order code: NANO 950 PMMA A4 (4% solid contents)
Molecular weight: 950 K
Solvent: in Anisole
Dehydration bake: 1 minutes at 170 deg.
Spinning: Program G on PMMA spinner

Speed: 4000rpm, Speed: 3000 rpm (for lift-off) [Please check the data sheet if one needs some other resist thickness]

Pre bake: 90 sec at 180 deg.

Exposure:
Acc voltage: 10KV
Dose: 80uC/cm2
Write field: 100um
Developer: IPA: MIBK::3:1, developing time: 30 s
Stopper: 2-propanol (IPA) pure, Stopping time: 15 s
Dry: with a low-nitrogen flow
PMMA thickness vs RPM

| Speed (rpm) | Thickness (nm) |
|---|---|
| 1500 | 754.75 |
| 2000 | 517.685 |
| 2500 | 275.0025 |
| 3000 | 247.435 |
| 3500 | 232.66 |
| 4000 | 212.62 |

B. Resist Type: HSQ (-ve) e-beam resist
Supplier order code: Dow Corning XR -1541 - 6%
Solvent: MIBK
Dehydration bake: 15 minutes at 170 deg.
Spinning: Program H on spinner 2

Speed: 4000rpm

Pre bake: 2 min at 250 deg.

Exposure:
Acc voltage: 10KV
Dose: 200uC/cm2
Write field: 100um
Developer: 25% TMAH , Developing time: 15s
Rinse: Flowing DI-Water, Rinsing time: 30s
Dry: with a low-nitrogen flow.